

Long wav length VCSEL

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*Con net drive***Abstract**

A VCSEL for emitting long wavelength light including a GaAs (111) substrate element (12), a first mirror stack (14) with mirror pairs in a GaAs/AlGaAs material system lattice matched to a GaInAsN active region (20) with an active structure (23) sandwiched between a first cladding region (24) adjacent the first mirror stack (14) and a second cladding region (25), the active structure (23) including a nitride based quantum well (35, 36, & 37), and a second mirror stack (26) lattice matched to the second cladding region (25) and

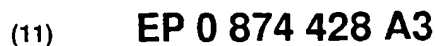
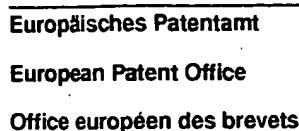
having mirror pairs in a GaAs/AlGaAs material system.



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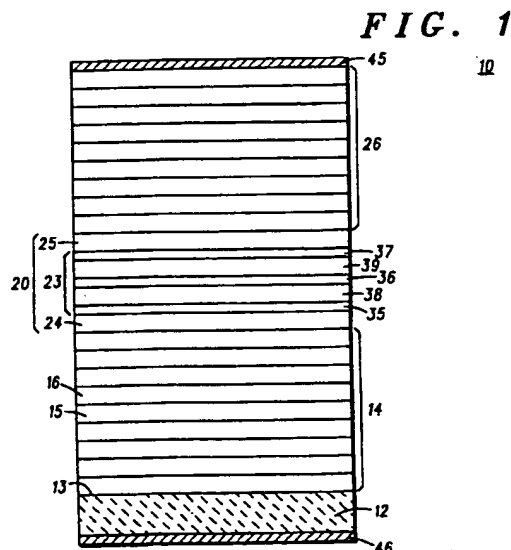
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(54) Long wavelength VCSEL

(57) A VCSEL for emitting long wavelength light including a GaAs (111) substrate element (12), a first mirror stack (14) with mirror pairs in a GaAs/AlGaAs material system lattice matched to a GaInAsN active region (20) with an active structure (23) sandwiched between a first cladding region (24) adjacent the first mirror stack (14) and a second cladding region (25), the active structure (23) including a nitride based quantum well (35, 36, & 37), and a second mirror stack (26) lattice matched to the second cladding region (25) and having mirror pairs in a GaAs/AlGaAs material system.



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European Patent
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EUROPEAN SEARCH REPORT

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EP 98 10 6843

DOCUMENTS CONSIDERED TO BE RELEVANT			
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int.Cl.6)
Y	T MIYAMOTO, T. TAKADA, ET AL: "Design and expected characteristics of 1.3 mum GaInNAs/GaAs vertical cavity surface emitting lasers" QUANTUM OPTOELECTRONICS 1997, TECHNICAL DIGEST SERIES, POSTCONFERENCE EDITION, vol. 9, 19 - 21 March 1997, page 126-128 XP002075850 Incline Village NV USA * the whole document *	1-9	H01S3/19 H01S3/085
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A	KONDOW M ET AL: "A NOVEL MATERIAL OF GAINAS FOR LONG-WAVELENGTH-RANGE LASER DIODES WITH EXCELLENT HIGH-TEMPERATURE PERFORMANCE" INTERNATIONAL CONFERENCE ON SOLID STATE DEVICES AND MATERIALS, 21 August 1995, pages 1016-1018, XP000544869 * the whole document *	1-9	TECHNICAL FIELDS SEARCHED (Int.Cl.6) H01S
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The present search report has been drawn up for all claims			
Place of search THE HAGUE		Date of completion of the search 28 August 1998	Examiner Claessen, L
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